

Novel Quasi-2D Perovskites for Stable and Efficient Perovskite Solar Cells

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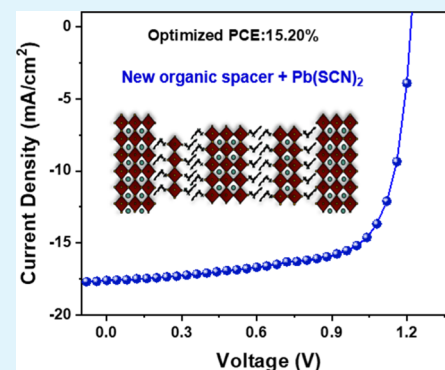
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Supporting Information

ABSTRACT: Compared to three-dimensional (3D) organic–inorganic hybrid perovskites, two-dimensional (2D) ones possess great possibilities to realize stable cost-effective perovskite solar cells (PSCs). However, studies indicated that PSCs with 2D perovskites exhibited poor power conversion efficiencies (PCEs). In this study, we report novel propargylamine cation (PPA^+)-based quasi-2D perovskites. PPA^+ employed as an organic spacer is for enhancing charge-carrier transport of quasi-2D $(\text{PPA})_2(\text{CH}_3\text{NH}_3)_2\text{Pb}_3\text{I}_{10}$ thin films, consequently boosting PCEs of PSCs. To further boost PCEs of PSCs with quasi-2D $(\text{PPA})_2(\text{CH}_3\text{NH}_3)_2\text{Pb}_3\text{I}_{10}$ thin films, a quasi-2D $(\text{PPA})_2(\text{CH}_3\text{NH}_3)_2\text{Pb}_3\text{I}_{10}$ thin film is processed with $\text{Pb}(\text{SCN})_2$ additives. Systematical studies indicate that the quasi-2D $(\text{PPA})_2(\text{CH}_3\text{NH}_3)_2\text{Pb}_3\text{I}_{10}$ thin film processed with $\text{Pb}(\text{SCN})_2$ additives exhibits superior film morphology and crystallinity, larger crystals, reduced nonradiative charge-carrier recombination, and enhanced and balanced charge-carrier mobilities compared to the pristine quasi-2D $(\text{PPA})_2(\text{CH}_3\text{NH}_3)_2\text{Pb}_3\text{I}_{10}$ thin film. As a result, PSCs with the quasi-2D $(\text{PPA})_2(\text{CH}_3\text{NH}_3)_2\text{Pb}_3\text{I}_{10}$ thin film processed with $\text{Pb}(\text{SCN})_2$ additives exhibit a PCE of 15.20%, which is an over 25% enhancement compared to those (12.16%) with a pristine quasi-2D $(\text{PPA})_2(\text{CH}_3\text{NH}_3)_2\text{Pb}_3\text{I}_{10}$ thin film. In addition, PSCs with the quasi-2D $(\text{PPA})_2(\text{CH}_3\text{NH}_3)_2\text{Pb}_3\text{I}_{10}$ thin film processed with $\text{Pb}(\text{SCN})_2$ additives possess dramatically suppressed photocurrent hysteresis and significantly boosted stability. All these results indicate that we have developed a facile way to synthesize novel 2D perovskite thin films for realizing stable and efficient PSCs with dramatically suppressed photocurrent hysteresis.

KEYWORDS: perovskite solar cells, 2D perovskite materials, propargylamine organic spacer, $\text{Pb}(\text{SCN})_2$ process additives, efficiency and stability



INTRODUCTION

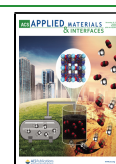
Organic–inorganic hybrid perovskites with a general chemical formula of ABX_3 , where A is methylammonium (MA^+), formamidinium (FA^+), or Cs^+ ; B is Pb^{2+} or Sn^{2+} ; and X is Cl^- , Br^- , or I^- or their combination, have drawn the greatest attention in both academic and industrial sectors because of their superior optoelectronic and photovoltaic properties.^{1–6} Over 25% power conversion efficiencies (PCEs) have been reported from perovskite solar cells (PSCs) with three-dimensional (3D) perovskites.⁷ Despite all of the astonishing progress made in the past decade, the intrinsic environmental instability issue of 3D perovskites needs to be addressed for further development and commercialization of PSCs.⁸ There exist prior reports of two-dimensional (2D) layered perovskites, crafted using organic cations, for example, butylammonium (BA^+) and phenethylammonium (PEA^+), substituting either MA^+ or FA^+ , that exhibited environmental stability, but possessed poor photovoltaic properties.^{9–15} PCEs of 8.13 and 9.66% were reported for PSCs with either BA^+ - or PEA^+ -based 2D perovskites with lower n values (where n is the stacking number of the $[\text{BX}_6]$ network layers between two organic barrier layers),^{9–15} respectively. Such low PCEs were ascribed

to poor charge-carrier transport of BA^+ - or PEA^+ -based 2D perovskites.^{14–16} Thus, the development of efficient organic spacers and understanding the charge transport mechanism are very important to further boost PCEs of PSCs. Recently, a PCE of 17.39% was reported for PSCs through alternating the ordering of diammonium (BEA^{2+}) and monoammonium (MA^+) cations in the interlayer space to form low-dimensional perovskites.¹⁷ Xu et al.¹⁸ reported two multiple-ring spacer cations, 1-naphthalenemethylammonium and 9-anthracenemethylammonium organic spacers, and further reported a PCE of 17.25% ($n = 4$) from PSCs. More recently, a PCE of 19.06% ($n = 5$) was further reported for PSCs with a 2D perovskite processed with an organic salt 4-(trifluoromethyl)-benzylammonium iodide.¹⁹ Nevertheless, a PCE of >15% for PSCs with 2D perovskites with $n < 4$ was rarely reported.²⁰

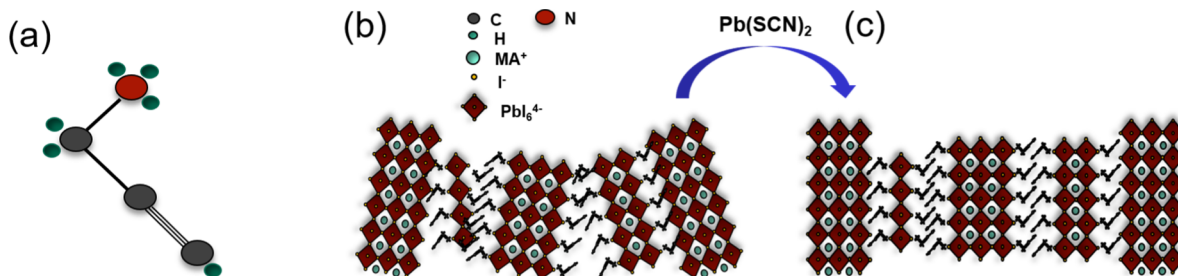
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Scheme 1. (a) Schematic Illustrations of the PPA⁺ Cation (Gray, Green, and Red Balls Represent C, H, and N Atoms, Respectively) and Realignment of the Quasi-2D Perovskite Crystal: (b) Pristine (Gray, Green, Light Green, and Yellow Balls Represent C, H, Atoms, and MA⁺ and I[−], Respectively) and (c) Processed with Pb(SCN)₂ Additives



In this study, we report novel propargylamine (PPA⁺)-based quasi-2D perovskites, where propargylamine (PPA⁺), a new organic spacer cation, is employed to prepare a quasi-2D (PPA)₂(CH₃NH₃)₂Pb₃I₁₀ thin film for enhancing its charge-carrier transport, consequently boosting PCEs of PSCs. To further enhance the crystallinities of the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film, a quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film is processed with Pb(SCN)₂ additives. Systematical studies indicate that the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with Pb(SCN)₂ additives possesses higher crystallinity, larger crystals, superior film morphology, reduced nonradiative recombination, and enhanced and balanced charge-carrier mobilities. As a result, the PSC with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with Pb(SCN)₂ additives exhibits a PCE of 15.20%, which is an over 25% enhancement compared with that (12.16%) with the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film. Moreover, PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with Pb(SCN)₂ additives exhibit dramatically boosted stability and suppressed photocurrent hysteresis.

EXPERIMENTAL SECTION

Materials. Propargylamine hydrochloride (PPA-HCl), lead(II) thiocyanate (Pb(SCN)₂), molybdenum(VI) oxide (99.97%), poly-[bis(4-phenyl)(2,4,6-trimethylphenyl)amine] (PTAA), dimethylformamide (DMF, anhydrous, 99.8%), dimethyl sulfoxide (DMSO, anhydrous, 99.9%), toluene (anhydrous, 99.8%), and aluminum slug were purchased from Sigma-Aldrich. Poly(3,4-ethylenedioxythiophene)polystyrene sulfonate (PEDOT:PSS) (SCA 388-20) was purchased from Heraeus. Lead iodide (PbI₂, 99.9985% metals basis) and tin oxide (15% in water colloidal dispersion) were purchased from Alfa Aesar. C₆₀ (99.95% carbon powder) was purchased from Purece60oliveoil. Methyl-ammonium iodide (MAI) was purchased from Greatcell Solar. All materials are used as received without any further treatment.

Preparation of Precursor Solutions. The quasi-2D perovskite precursor solution was prepared by mixing of Pb(SCN)₂, PPA-HCl, MAI, and PbI₂ with a stoichiometric ratio of *x*:2:2:3 (where *x* is the Pb(SCN)₂ content) into 1 M DMF/DMSO (volume ratio of 4:1) solution. The perovskite precursor solution for making the 3D CH₃NH₃PbI₃ thin film was prepared in a stoichiometric ratio of 1:1 for MAI and PbI₂ into 1 M DMF/DMSO (volume ratio of 4:1) solution. All perovskite precursor solutions were thoroughly mixed and aged for 12 h before use.

Preparation of Quasi-2D and 3D Perovskite Thin Films. Precleaned quartz (or glass) substrates were treated with UV-ozone plasma for about 20 min. The quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ and 3D CH₃NH₃PbI₃ thin films were prepared by a one-step method with a spin speed of 4000 rpm for 30 s. To make a homogenous thin film, the dropped perovskite precursor solutions should completely cover the surface of substrates. After that, thin films were thermally annealed

at 100 °C for 10 min and then cooled down to room temperature naturally.

Characterization of Perovskite Thin Films. The X-ray diffraction (XRD) patterns were obtained by Rigaku SmartLab XRD. The absorption spectra were characterized using a Lambda 900 UV-vis-NIR spectrophotometer (PerkinElmer, Waltham, MA, USA). The photoluminescence (PL) spectra were obtained using a QuantaMaster 2361 (HORIBA). Scanning electron microscopy (SEM) images were obtained using field-emission SEM (model JEOL-7401). The thicknesses were measured using a Bruker DektakXT Stylus profilometer with a scan rate of 0.03 mm s^{−1}. Grazing-incidence wide-angle X-ray scattering (GIWAXS) was performed on the dedicated high-resolution GIWAXS beamline (Sector 8-ID-E) in the Advanced Photon Source, Argonne National Laboratory, at an incident angle of 0.14°. The GIWAXS data were collected by exposing the samples to X-rays for 10 s, and the collected data were analyzed using MATLAB-based software (GIXSGUI). Individual 3D MAPbI₃ thin films, quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films, and the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives were imaged using total internal reflection fluorescence microscopy (TIRFM) under a wavelength of 532 nm laser excitation. The excitation laser intensities were 0.25 mW. The PL of perovskite particles was filtered using a 542 nm long-pass filter and a 585/65 nm single bandpass filter and collected using a sCMOS camera. Under each experimental condition, 1000 consecutive images of perovskite particles were taken with the exposure time set to 10 ms.

Fabrication of PSCs with Quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ Thin Films. Precleaned ITO/glass substrates were treated with UV-ozone plasma for about 20 min, where ITO is indium tin oxide. Then, a ~20 nm PTAA thin film was spin-cast on the top of ITO/glass substrates with a spin speed of 6000 rpm for 30 s from 2 mg/mL PTAA toluene solution, followed by thermal annealing at 100 °C for 10 min. After the PTAA-coated substrates were cooled down to room temperature, the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film was prepared by a one-step method as described above. Afterward, ~40 nm C₆₀ was thermally deposited on the top of the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film in a vacuum system with a base pressure of 10^{−6} Torr. PSCs were completed by thermal deposition of ~100 nm Al on the top of the C₆₀ layer in a vacuum system. The device area was measured to be 0.045 cm².

Characterization of PSCs. The current densities versus voltages (*J*–*V*) characteristics of PSCs were tested using a Keithley model 2400 source measure unit. The light source was a Newport Air Mass 1.5 Global (AM1.5G) full-spectrum simulator with a light intensity of 100 mW·cm^{−2}, which was calibrated by utilizing a monosilicon detector (with a KG-5 visible color filter) from the National Renewable Energy Laboratory to reduce the spectral mismatch. The external quantum efficiency (EQE) spectrum was obtained on a solar cell quantum efficiency measurement system (QEX10). Impedance spectroscopy (IS) was conducted using an HP 4194A impedance/gain-phase analyzer under illumination and in the dark, at the voltage closing to a *V*_{OC} condition. The frequency is varied from 5 to 105 Hz. Both capacitance–voltage (*C*–*V*) and capacitance–frequency (*C*–*F*) testing were also performed using the same setup. The transient

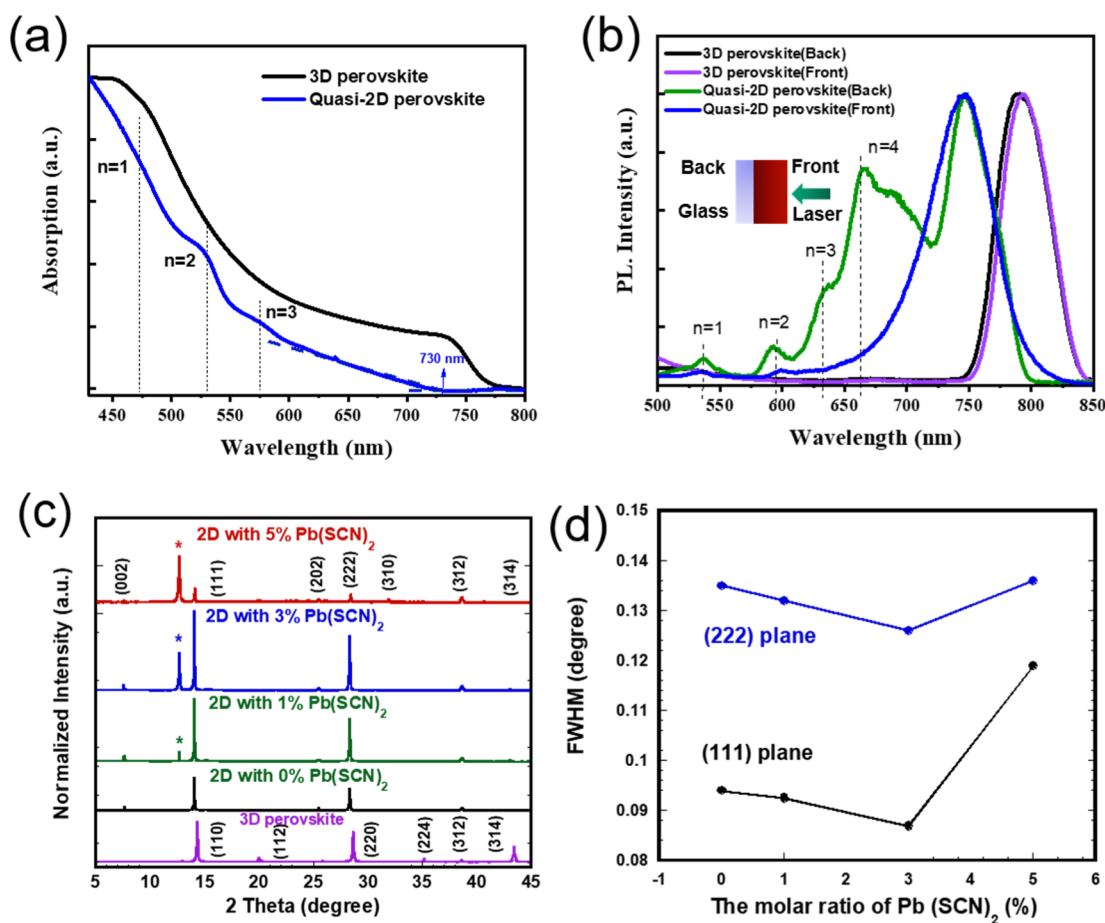


Figure 1. (a) Absorption spectra of the 3D MAPbI₃ thin film and quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film and (b) PL spectra of the 3D MAPbI₃ thin film and quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film measured from the back and front side, excited at a wavelength of 420 nm. (c) XRD patterns of the 3D MAPbI₃ thin film, pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film, and quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films processed with Pb(SCN)₂ additives. The star indicates the impurities of PbI₂. (d) fwhms for the (111) and (222) planes from the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films processed with Pb(SCN)₂ additives.

photocurrent (TPC) measurement was done using a homemade setup in our laboratory.^{8,21,22}

RESULTS AND DISCUSSION

The molecular structures of the PPA⁺ cation and the corresponding quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ perovskites are schematically displayed in Schemes 1a,b. The nominal *n*-value (3) in this work is estimated based on the stoichiometry of precursors. PPA⁺ is employed as an organic spacer to form 2D perovskite thin films because the carbon–carbon triple bond (C≡C) in the PPA⁺ molecule could prevent intramolecular hydrogen bonds and decrease the alkalinity and nucleophilicity of –NH₂. Moreover, PPA⁺ has a shorter chain length than that of either BA⁺ or PEA⁺.^{9–15} Such a short-chain length could facilitate charge carriers to be efficiently transported within (PPA)₂(MA)₂Pb₃I₁₀ thin films, resulting in boosted charge-carrier transport within (PPA)₂(MA)₂Pb₃I₁₀ thin films.^{14–16} As a result, high short circuit photocurrent (*J*_{SC}) is anticipated to be observed from PSCs with (PPA)₂(MA)₂Pb₃I₁₀ thin films.

Figure 1a displays the absorption spectra of the (PPA)₂(MA)₂Pb₃I₁₀ thin film and 3D MAPbI₃ thin film casted on the quartz substrates. Based on the absorption spectrum, the optical bandgap of the (PPA)₂(MA)₂Pb₃I₁₀ thin film is calculated to be 1.70 eV, which is larger than that (1.59 eV) for the 3D MAPbI₃ thin film. It is clear that the absorption

spectrum of the (PPA)₂(MA)₂Pb₃I₁₀ thin film is different to that of the 3D MAPbI₃ thin film. Moreover, the characteristic exciton peaks of the (PPA)₂(MA)₂Pb₃I₁₀ thin film for *n* = 1, 2, and 3 are located at 471, 529, and 575 nm, respectively, which indicates that strong quantum confinement takes place in the (PPA)₂(MA)₂Pb₃I₁₀ thin film.

Figure 1b presents the PL spectra of (PPA)₂(MA)₂Pb₃I₁₀ and 3D MAPbI₃ thin films casted on the glass substrates, measured from both the front (air) side and the back (glass) side, under the same monochromatic light excitation at a wavelength of 420 nm. The PL spectrum of the 3D MAPbI₃ thin film measured from the back side is nearly identical to that measured from the front side. However, the PL spectrum of the (PPA)₂(MA)₂Pb₃I₁₀ thin film measured from the front side is dramatically different to that from the back side, which indicates that multiple perovskite phases (*n*) coexist within the (PPA)₂(MA)₂Pb₃I₁₀ thin film.^{14–16} Moreover, compared with the PL spectrum of the (PPA)₂(MA)₂Pb₃I₁₀ thin film measured from the back side, the PL spectrum of the thin film measured from the front side exhibit four obvious intense peaks, which correspond to *n* = 4, 3, 2, and 1, respectively.^{9,10} These significant differences demonstrate that the layered perovskite phases with smaller *n* is probably preferably formed at the bottom, while the perovskite phases with a larger *n* (3D phase) is probably preferably formed at the surface of the thin

film.¹³ In addition, the blue-shifted PL spectrum observed from the (PPA)₂(MA)₂Pb₃I₁₀ thin film compared to that of the 3D MAPbI₃ thin film further confirms that strong quantum confinement takes place in the (PPA)₂(MA)₂Pb₃I₁₀ thin film.

In addition, the exciton binding energies of the 3D MAPbI₃ thin film and (PPA)₂(MA)₂Pb₃I₁₀ thin film are further estimated. The exciton binding energies are estimated by a difference between the optical energy gap and the exciton energy gap, $\Delta E = E_{\text{opt}} - E_{\text{ex}}$,²³ where E_{opt} is the optical energy gap and E_{ex} is the exciton energy gap. Based on the absorption cut-off and PL peak, the exciton binding energy of the 3D MAPbI₃ thin film is estimated to be 30 meV; whereas the exciton binding energies of the (PPA)₂(MA)₂Pb₃I₁₀ thin film are estimated to be 320, 260, 190, and 50 meV, for $n = 1, 2, 3$, and ∞ , respectively. Thus, it is concluded that the (PPA)₂(MA)₂Pb₃I₁₀ thin film is with a quasi-2D structure rather than with a pure 2D structure.¹⁰ The optoelectronic properties of 3D MAPbI₃ and quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films are summarized in Table 1.

Table 1. Optoelectronic Properties of 3D MAPbI₃ and Quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ Thin Films

perovskite thin films	optical band gap (eV)	exciton energy (eV)	exciton binding energy (meV)
quasi-2D ($n = 1$) phase	2.63	2.31	320
quasi-2D ($n = 2$) phase	2.34	2.08	260
quasi-2D ($n = 3$) phase	2.15	1.96	190
quasi-2D ($n = \infty$) phase	1.70	1.65	50
3D perovskite	1.59	1.56	30

Figure 1c shows the XRD patterns of the 3D MAPbI₃ thin film and quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films casted on glass substrates. The (110), (112), (220), (224), (312), and (314) planes observed from the 3D MAPbI₃ thin film and the (111), (202), (222), (310), (312), and (314) planes observed from the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film demonstrate that both of them possess a typical tetragonal structure.⁴ However, the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film possesses

a peak located at a 2θ of $\sim 7^\circ$, corresponding to the (002) plane, which is the characteristic feature of 2D perovskites.⁹ These results further confirm that the (PPA)₂(MA)₂Pb₃I₁₀ thin film possesses a quasi-2D structure.^{17–20}

To further enhance the crystallinities of quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films, quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films are processed from their corresponding precursor solutions mixed with Pb(SCN)₂ additives. Pb(SCN)₂ is selected as the processing additives because it is a Lewis base, which could interact with under-coordinated Pb atoms and halide vacancies as well, tuning the perovskite crystal growing processes. Note that the excess SCN[−] would form HSCN gas to be finally removed from quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films during the thermal annealing process because HSCN possesses a low boiling point (-87.78°C).^{24,25} A schematic illustration of perovskite crystal growth processes tuned by Pb(SCN)₂ additives is proposed in Scheme 1b,c. Thus, the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films processed with Pb(SCN)₂ additives are expected to possess better crystallinity.

To verify the abovementioned hypothesis, XRD is carried out to study the crystal structure of the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films processed with Pb(SCN)₂ additives and the results are also shown in Figure 1c. The quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films processed with Pb(SCN)₂ additives possess the same lattice planes as the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film does. In addition, a refraction peak corresponding to PbI₂ crystals is presented within the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films processed with Pb(SCN)₂ additives, and the peak intensities increased with increasing concentrations of Pb(SCN)₂ additives. These results indicate that extra Pb²⁺ from Pb(SCN)₂ additives interacts with I[−], forming PbI₂ crystals.

Moreover, it is found that the peak intensities of the lattice planes for the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films processed with Pb(SCN)₂ additives increased and then decreased with increasing concentrations of Pb(SCN)₂ additives. The full width at half-maximums (fwhms) of the (111) and (222) planes for the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films processed with Pb(SCN)₂ additives are calculated and the results are shown in Figure 1d. Both fwhm values of

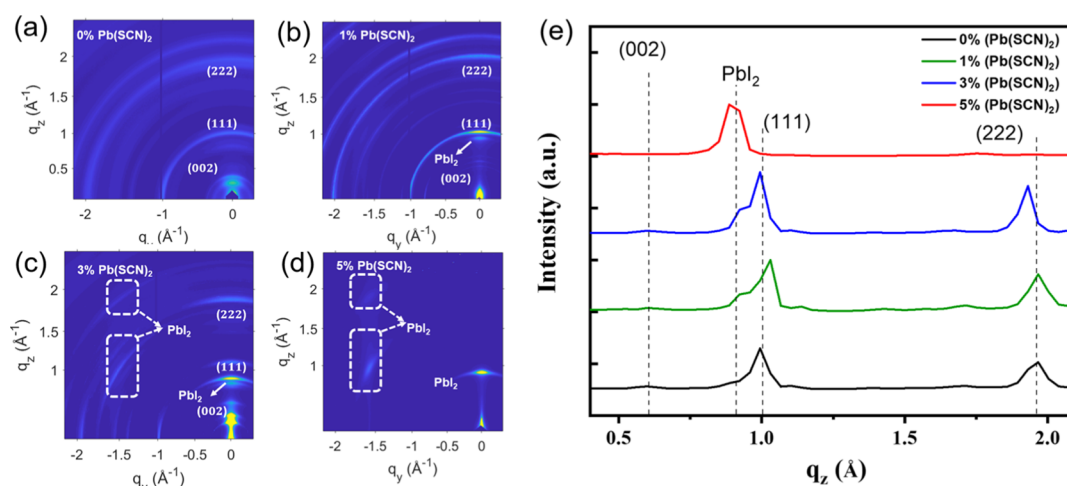


Figure 2. 2D GIWAXS profiles of (a) pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film and quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films processed with (b) 1% Pb(SCN)₂, (c) 3% Pb(SCN)₂, and (d) 5% Pb(SCN)₂ additives and (e) 1D GIWAXS line profiles extracted from (a–d) (out-of-plane direction, incident angle of 0.14°).

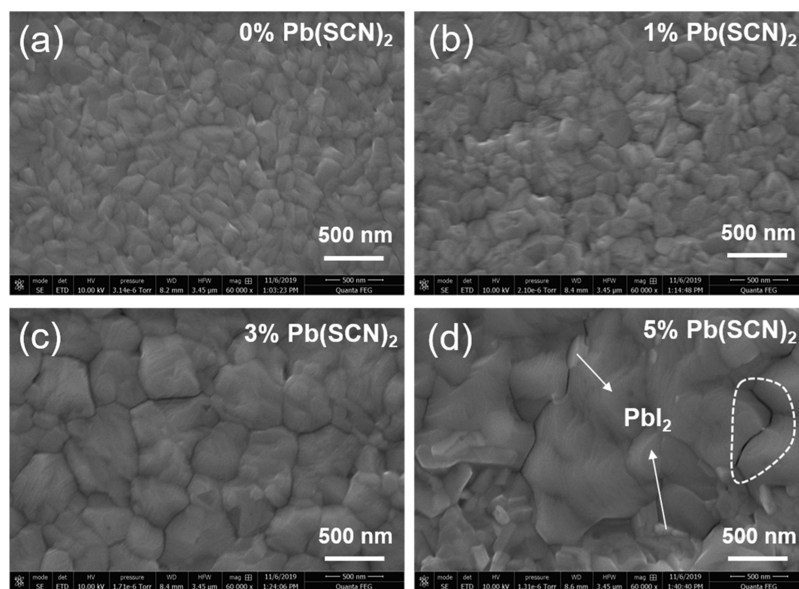


Figure 3. SEM images of (a) pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film and quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films processed with (b) 1% $\text{Pb}(\text{SCN})_2$, (c) 3% $\text{Pb}(\text{SCN})_2$, and (d) 5% $\text{Pb}(\text{SCN})_2$ additives, respectively.

the (111) and the (222) planes decreased for the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films processed with either 1 or 3% of $\text{Pb}(\text{SCN})_2$ additives and then increased with 5% of $\text{Pb}(\text{SCN})_2$ additives. The decreased fwhm values indicate that the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films processed with low concentrations of $\text{Pb}(\text{SCN})_2$ additives possess an optimal crystallinity with few crystal imperfections and structural defects, and the increased fwhm value indicates that the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with high concentrations of $\text{Pb}(\text{SCN})_2$ additives exhibits poor crystallinity.²⁶ Thus, the XRD results confirm that $\text{Pb}(\text{SCN})_2$ processing additives could effectively tune the crystalline features, resulting in high-quality quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films as the concentration of $\text{Pb}(\text{SCN})_2$ additives is lower than 5%.

Figure 2a–d displays the orientation of the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films processed with $\text{Pb}(\text{SCN})_2$ additives investigated by GIWAXS. The quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films show randomly oriented features for the (111) and (222) planes (Figure 2a). Clearly visible spots in the ring with oriented crystals are observed from the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films processed with both 1% and 3% $\text{Pb}(\text{SCN})_2$ additives (Figure 2b,c), which indicates that these crystals are oriented.^{6,26} However, the PbI_2 impurity peak is visible within the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films processed with 3% $\text{Pb}(\text{SCN})_2$ additives. Moreover, the PbI_2 impurity peak is obviously observed from the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 5% $\text{Pb}(\text{SCN})_2$ additives (Figure 2d), which indicates that there is quite an amount of PbI_2 clusters within quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films.

Figure 2e shows the 1D GIWAXS line profiles of the pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film and the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films processed with $\text{Pb}(\text{SCN})_2$ additives, which are extracted from the out-of-plane directions of 2D GIWAXS. The increased intensities of the (111) and the (222) peaks observed from the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films processed with both 1 and 3% $\text{Pb}(\text{SCN})_2$ additives indicate that the (111) and (222) planes are more oriented in

these quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films. However, both the (111) and (222) planes disappeared in the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 5% $\text{Pb}(\text{SCN})_2$ additives. This is probably ascribed to the fact that these disappeared planes are overaged by the excess of PbI_2 clusters at the surface of the resultant quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film. The lattice planes corresponding to the PbI_2 clusters are nearby the (111) plane, and the strong refraction from the PbI_2 clusters probably covers the (111) plane.

Figure 3 displays the top-view SEM images of quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films casted on the PTAA/ITO/glass substrates. A smooth and full-coverage film with densely packed crystalline grains and ~ 100 nm crystal size is observed for pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film. The quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 1% $\text{Pb}(\text{SCN})_2$ additives maintains the features as the pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film does, but with dramatically enlarged crystal size (~ 300 nm). Furthermore, the crystal grain sizes of the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives are enlarged to ~ 500 nm. The quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 5% $\text{Pb}(\text{SCN})_2$ additives exhibit even larger crystal sizes (over 700 nm), but with considerable amounts of voids and pinholes. All these results demonstrate that the $\text{Pb}(\text{SCN})_2$ processing additives could effectively tune the crystallinities of quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films and promote the growth of large perovskite crystals.

In addition, as indicated in Figure 3d, small PbI_2 clusters are present in the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 5% $\text{Pb}(\text{SCN})_2$ additives, but such PbI_2 clusters are too small to be found in the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives. These PbI_2 clusters probably appear at the surface of the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 5% $\text{Pb}(\text{SCN})_2$ additives, whereas few smaller PbI_2 clusters are probably randomly well-distributed in the bulk of quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin films processed with 3% $\text{Pb}(\text{SCN})_2$.

TIRFM is further carried out to investigate PL profiles of individual perovskite particles.²⁷ Figure 4 presents the PL

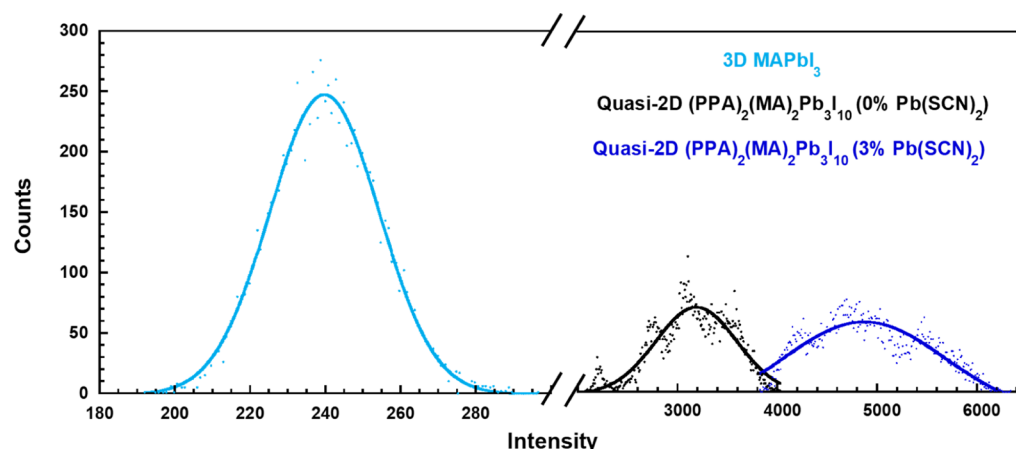


Figure 4. PL intensity histogram of TIRFM for individual perovskite particles of the 3D MAPbI₃ thin film, pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film, and quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives.

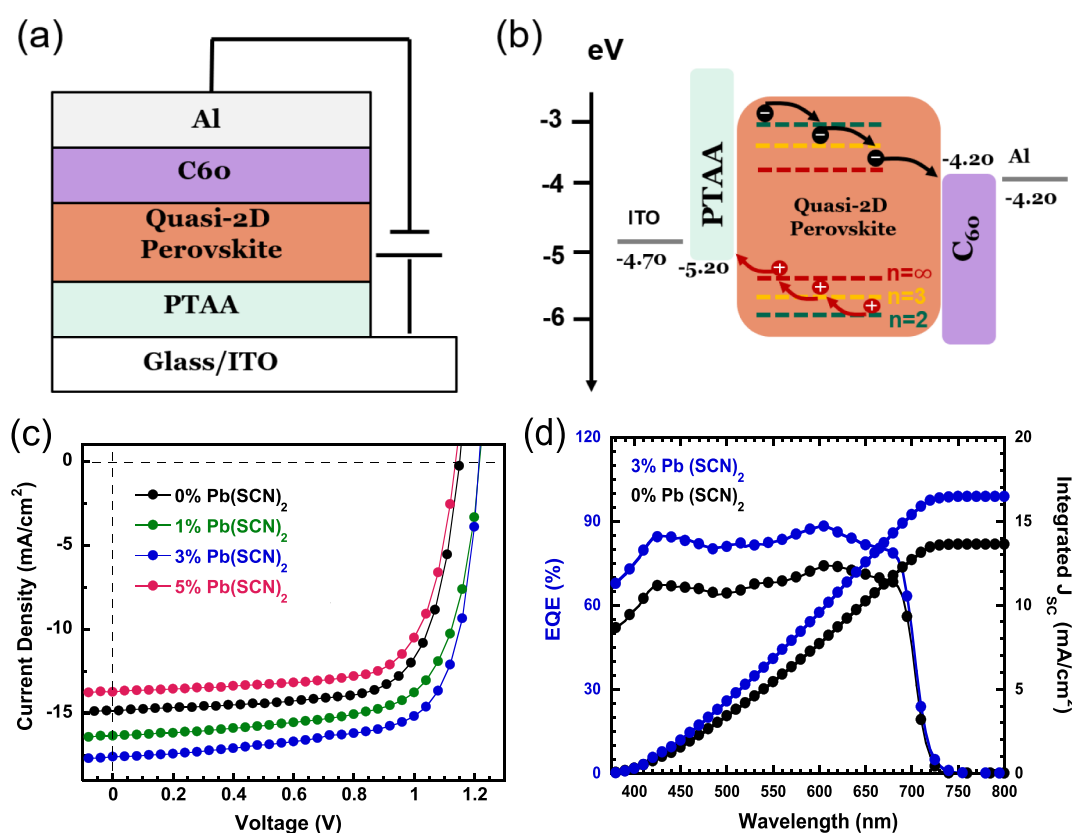


Figure 5. (a) Device structure of PSCs and (b) CBs and VBs of the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film, the LUMO and HOMO energy levels of PTAA and C₆₀, and the work functions of ITO and Al. (c) *J*–*V* characteristics of PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with Pb(SCN)₂ additives and (d) EQE spectra and the integrated photocurrent density of PSCs with either the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film or the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives.

intensity histogram of TIRFM for individual perovskite particles of the 3D MAPbI₃ thin film, the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film, and the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives, which can also be observed from TIRFM images shown in Supporting Information 1. Compared to the PL intensity of 3D MAPbI₃ perovskite particles ($\mu = 240$, where μ is the mean of distribution), the enhancement in PL intensity for perovskite particles of quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ ($\mu = 3188$) indicates a much stronger exciton binding energy, which further confirms that the (PPA)₂(MA)₂Pb₃I₁₀ thin film is with

a quasi-2D structure. In addition, it is clear that the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives ($\mu = 4872$) exhibits more intense PL compared to the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film ($\mu = 3188$). These observations demonstrate that the nonradiative recombination in the quasi-2D perovskite thin film processed with 3% Pb(SCN)₂ additives is dramatically suppressed. In addition, these observations are consistent with the SEM characteristics.

In order to verify that PPA⁺ with a short-chain length could facilitate efficient charge-carrier transport, charge-carrier

mobility of quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films is investigated through a single-carrier device based on the space charge limited current (SCLC) method, according to the Mott–Gurney law.^{28–31} The electron-only diode with a device structure of ITO/SnO₂/active layer/C₆₀/Al and the hole-only diode with a device structure of ITO/PEDOT:PSS/active layer/MoO₃/Ag, where the active layer is either the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film or the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives, respectively, are fabricated and characterized. As shown in Supporting Information 2, the *J*–*V* characteristics can be divided into the Ohmic region (*J* ∝ *V*) at low bias and the SCLC region (*J* ∝ *V*²) under high bias. The *J*–*V* curve in the SCLC region can be well-fitted by the Mott–Gurney law^{28–31}

$$J = \frac{9\epsilon\epsilon_0\mu V^2}{8L^3} \quad (1)$$

where μ is the charge-carrier mobility, *V* is the external bias, *L* is the thickness of the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film, ϵ_0 is the vacuum permittivity, and ϵ is the dielectric constant for quasi-2D (PPA)₂(MA)₂Pb₃I₁₀, which is described by^{28–31}

$$C = \epsilon\epsilon_0 \frac{A}{d} \quad (2)$$

where *A* is the device area and *d* is the film thickness of the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film. The capacitance versus frequency characteristics of photodiodes with a device structure of ITO/active layer (~350 nm)/Al, where the active layer is either the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film or the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives, are studied and characterized (Supporting Information 2). According to eq 2, the ϵ values are calculated to be 5.4 and 5.5 for the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film and the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives, respectively. Thus, based on eq 1, the electron and hole mobilities of pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film are calculated to be 9.34×10^{-4} and 4.51×10^{-3} cm² V⁻¹ s⁻¹, respectively ($\mu_e/\mu_h = 0.21$). Both hole mobility and electron mobility of the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film are higher than the reported values (e.g., a hole mobility of 1.5×10^{-4} cm² V⁻¹ s⁻¹ and an electron mobility of $\sim 10^{-4}$ cm² V⁻¹ s⁻¹ for BA-based quasi-2D perovskites; a hole mobility of 2.8×10^{-5} cm² V⁻¹ s⁻¹ and an electron mobility of 2.5×10^{-3} cm² V⁻¹ s⁻¹ for PEA-based quasi-2D perovskites).^{32,33} Such boosted charge-carrier mobilities are attributed to a shorter chain length of the organic spacer PPA⁺ compared with that of either BA⁺ or PEA⁺ spacers. Moreover, the electron and hole mobilities of the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives are calculated to be 7.45×10^{-3} and 8.72×10^{-3} cm² V⁻¹ s⁻¹, respectively, which indicates that charge-carrier transport is tended to be balanced ($\mu_e/\mu_h = 0.85$). It is clear that the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives possesses both enhanced and balanced charge-carrier mobilities compared to the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film. Therefore, enhanced *J*_{SC} is expected to be observed for PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives.

The photovoltaic properties of quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films are investigated through the characterization of PSCs with a device configuration of ITO/PTAA/quasi-2D (PPA)₂(MA)₂Pb₃I₁₀/C₆₀/Al, as shown in Figure 5a, where ITO acts as the anode, PTAA acts as the hole extraction layer (HEL), C₆₀ is used as the electron extraction layer (EEL) and the hole blocking layer, and Al acts as the cathode, respectively. The highest occupied molecular orbit (HOMO) energy levels and the lowest unoccupied molecular orbit (LUMO) energy levels of PTAA and C₆₀, the conduction band (CB) and valence band (VB) of quasi-2D (PPA)₂(MA)₂Pb₃I₁₀, and the work functions of the ITO anode and the Al cathode are shown in Figure 5b. As indicated in Figure 1b, the layered perovskite phases with smaller *n* are preferably formed at the bottom, while those with larger *n* (3D phase) are preferably formed at the surface of the thin film, indicating that multiple energetic states coexist in quasi 2D perovskite thin films. Both CB and VB energy levels of the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film from a low *n* value to a high *n* value exhibit a stepwise alignment, which indicates that the photogenerated electrons and holes could be effectively extracted from quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films. Moreover, a HOMO of -5.20 eV for the PTAA HEL and a LUMO of -4.20 eV for the C₆₀ EEL are well-matched with perovskites with an *n* value of ∞ (3D perovskite), leading to effective extraction of charge carriers from the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ active layer to the ITO anode and the Al cathode. Thus, a boosted *J*_{SC} from PSCs is anticipated.

The *J*–*V* characteristics of PSCs under AM1.5G illumination with a light intensity of 100 mW/cm², measured with a scan rate of 0.05 V s⁻¹, are shown in Figure 5c. The PSCs with the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film exhibit a *J*_{SC} of 14.84 mA·cm⁻², an open circuit voltage (*V*_{OC}) of 1.15 V, a fill factor (FF) of 71%, and a corresponding PCE of 12.16%. These device performance parameters are higher than those for PSCs with BA- and/or PEA-based quasi-2D perovskites,^{14,15} indicating that the carbon–carbon triple bond (C≡C) in the PPA⁺ molecule could prevent the formation of intramolecular hydrogen bonds and decrease the alkalinity and nucleophilicity of -NH₂, resulting in enhanced charge-carrier mobilities, consequently, and boosted device performance of PSCs. The PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 1% Pb(SCN)₂ additives exhibit a *J*_{SC} of 16.35 mA·cm⁻², a *V*_{OC} of 1.20 V, a FF of 70%, and a corresponding PCE of 13.78%. Moreover, the PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives exhibit a *J*_{SC} of 17.60 mA·cm⁻², a *V*_{OC} of 1.20 V, a FF of 72%, and a corresponding PCE of 15.20%, which is a 25% enhancement compared with that (12.16%) for the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film. Dramatically enhanced device performance is ascribed to higher crystallinity of the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films processed with Pb(SCN)₂ additives. However, the PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 5% Pb(SCN)₂ additives exhibit a *J*_{SC} of 13.77 mA·cm⁻², a *V*_{OC} of 1.12 V, a FF of 72%, and a corresponding PCE of 11.14%. Such a poor device performance is probably attributed to the excess amounts of voids and pinholes on the surface of the thin film (Figure 3d), leading to serious surface charge-carrier recombination, consequently resulting in poor device performance. In addition, excess of PbI₂ is also detrimental to device performance.³⁴ All these results are well consistent with the XRD analysis and SEM characterizations discussed above.

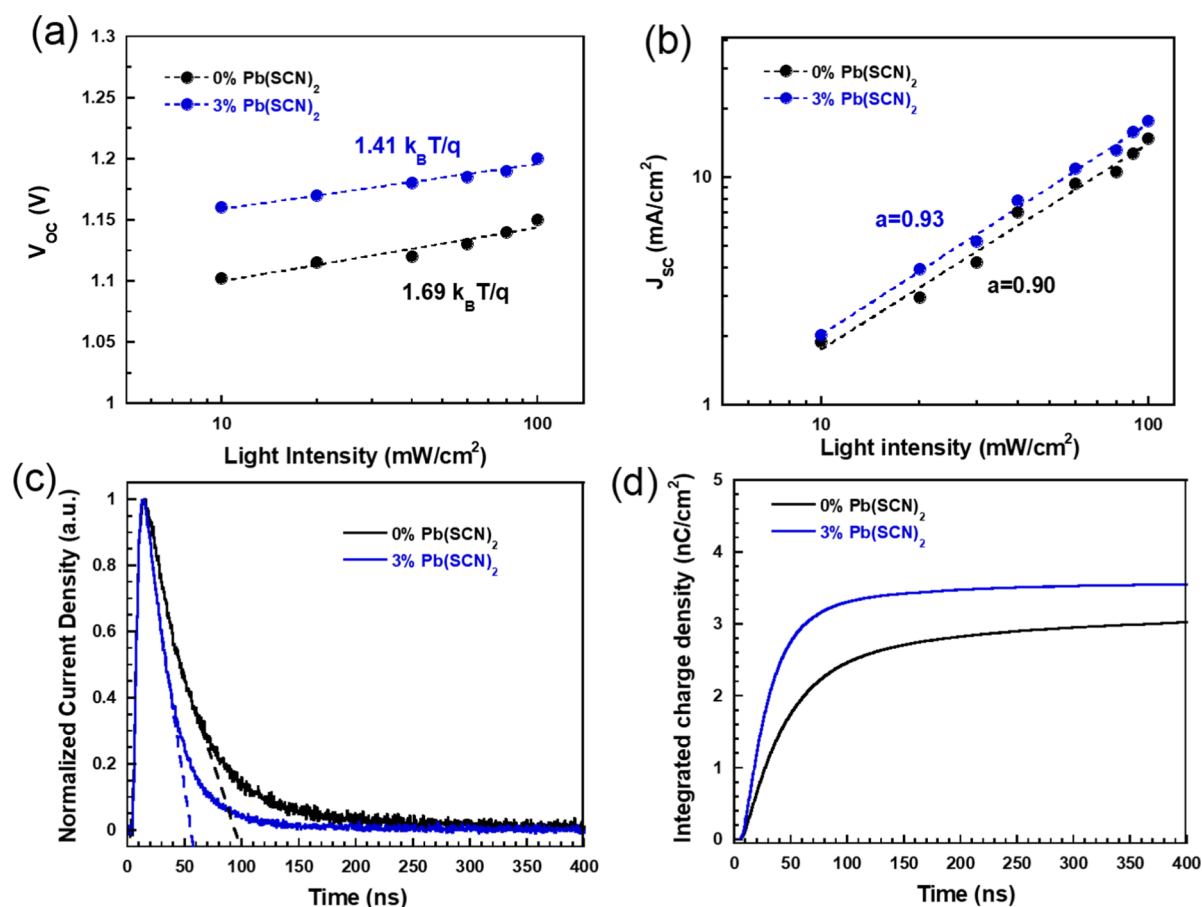


Figure 6. Light intensity dependence of (a) V_{OC} and (b) J_{SC} for PSCs with either the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film or the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives. (c) Normalized TPC curves and (d) integrated charge density curves of PSCs with either the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film or the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives, measured under -1 V applied bias at 590 nm wavelength.

Figure 5d shows the EQE spectra of PSCs. The PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives possess higher EQE values than those with the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film. Based on the EQE spectra, the integrated photocurrent densities are 13.61 and 16.46 mA/cm² for PSCs with the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film and PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives, respectively. The photocurrent densities obtained from the EQE spectra are consistent with J_{SC} values obtained from the J - V characteristics (Figure 5c). All these results demonstrate that Pb(SCN)₂ processing additives could effectively affect the electronic properties of quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films.

To understand the underlying physics of enlarged J_{SC} from PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives, IS is utilized to investigate the charge-carrier transport and recombination processes within PSCs.³⁵ Under 1 sun illumination at the voltage of V_{OC} , the charge transfer resistance (R_{CT}) of PSCs with the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film is calculated to be $\sim 281 \Omega$, whereas an R_{CT} of $\sim 235 \Omega$ is obtained for PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives. A small R_{CT} indicates that PSCs exhibit a large J_{SC} (Supporting Information 2).³⁶ Thus, compared with PSCs with the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film, PSCs with the quasi-2D

(PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives exhibit higher J_{SC} .

The charge-carrier recombination resistance (R_{rec}) values are further calculated from the IS spectra at low frequency measured in the dark (Supporting Information 2). The R_{rec} values of PSCs with the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film and PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives are ~ 5920 , and $\sim 7500 \Omega$, respectively. Clearly, a higher R_{rec} indicates that a weaker charge-carrier recombination takes place in PSCs.³⁶ Thus, compared with PSCs with the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film, PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives exhibit higher J_{SC} .

The light intensity dependence of V_{OC} is studied for further investigation charge-carrier recombination within PSCs.^{37,38} V_{OC} correlated with the light intensity is described as $V_{OC} \propto S \ln(I)$, where $S = (nk_B T)/q$ (where k_B is the Boltzmann constant, q is the elementary charge, T is the room temperature in Kelvin, and I is the light intensity).³⁷ As $n \approx 1$, the bimolecular recombination is dominant in solar cells, while as $n \approx 2$, the monomolecular recombination is dominant in solar cells.³⁷ The light intensity dependence of V_{OC} for PSCs is shown in Figure 6a. Both PSCs follow the relationship of $V_{OC} \propto S \ln(I)$. For PSCs with the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film, $S = 1.69 k_B T/q$, whereas for PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ processed with

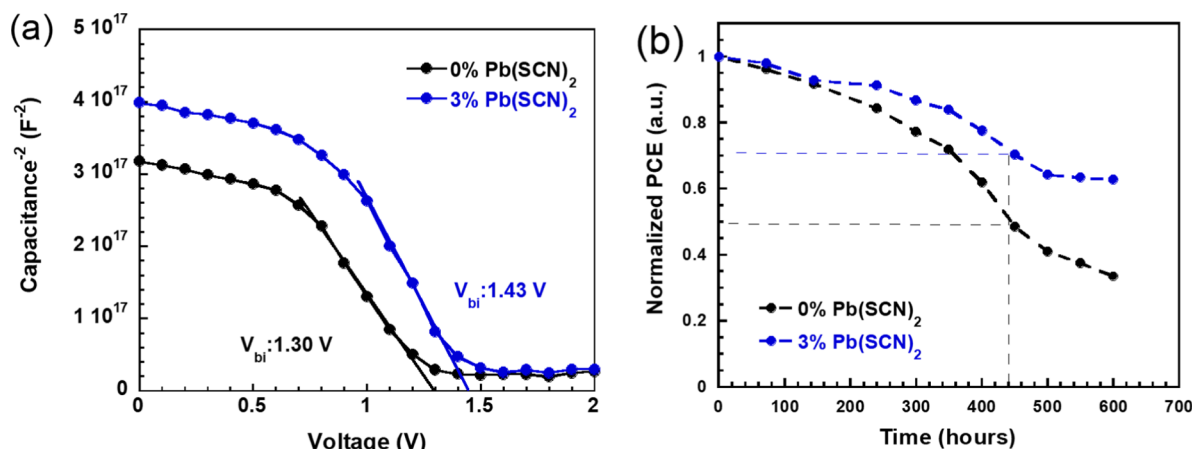


Figure 7. (a) Mott–Schottky analysis and (b) shelf stabilities of PSCs with either the pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film or the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives.

3% $\text{Pb}(\text{SCN})_2$ additives, $S = 1.41k_B T/q$. Thus, the monomolecular recombination is dominant in PSCs with the pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film, whereas PSCs with the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives possess less monomolecular recombination. As a result, a higher J_{SC} is observed for PSCs with the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives.

The light intensity dependence of J_{SC} for PSCs is shown in Figure 6b. All PSCs exhibit a power-law dependence of J_{SC} on the light intensity, which is described as $J_{\text{SC}} \propto I^\alpha$ (where I is the light intensity and α is the coefficient).^{37,38} As $\alpha = 1$, all charge carriers are swept out before recombination.^{37,38} α values of 0.90 and 0.93 are observed from PSCs with the pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film and PSCs with the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives, respectively. A larger α suggests that the bimolecular recombination is suppressed in PSCs with the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives. Thus, a larger J_{SC} is observed for PSCs with the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives.

TPC measurement is also carried out to investigate the charge-carrier extraction properties within PSCs. An external bias of -1 V is applied across PSCs to minimize the charge-carrier recombination.^{21,22} Figure 6c presents the normalized photocurrent density curves, which are collected at a wavelength of 590 nm. The charge extraction time is estimated by extrapolating the normalized transient current density from the linear region to zero.^{21,22} Charge-carrier extraction times of ~ 100 ns and ~ 60 ns are observed for PSCs with the pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film and PSCs with the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives, respectively. A shorter charge-carrier extraction time indicates that an efficient charge extraction process takes place within PSCs. Moreover, as shown in Figure 6d, the significantly enlarged extracted charge-carrier densities are observed for PSCs with the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives, which indicates that more charge carriers are generated compared with those with the pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film. All these results demonstrate that PSCs with the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$

additives possess higher J_{SC} compared with those with the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film.

The PL spectra of the $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film and quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives coated on the glass substrates measured from both the front (air) side and the back (glass) side are investigated (Supporting Information 3). It is found that the shape of PL spectra for both two thin films is nearly identical, but the PL intensity of the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives is slightly higher than that of the $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film, which indicates that reduced nonradiative recombination takes place in the $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives. These observations are consistent with the TIRFM results (Figure 4). In addition, an increased PL peak intensity, corresponding to the phase of $n = 5$ in the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives, from the back side is observed, which indicates that the distribution of n is indeed tuned by the addition of $\text{Pb}(\text{SCN})_2$.

Mott–Schottky analysis, based on the C – V measurement, is further carried out to investigate the built-in potentials (V_{bi}) of PSCs.^{39,40} As shown in Figure 7a, under forward bias, the V_{bi} of PSCs is extracted from $C^{-2} = \frac{2(V_{\text{bi}} - V)}{q\epsilon\epsilon_0 A^2 n_{\text{trap}}}$ (where ϵ is the dielectric constant, ϵ_0 is the vacuum permittivity, and A is the active area) by extrapolating the linear fitting line to the intercept on the x -axis.⁶ A V_{bi} of ~ 1.43 V is observed for PSCs with the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives, whereas a V_{bi} of ~ 1.30 V is observed for PSCs with the pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film. Therefore, as expected, PSCs with the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives exhibit a larger V_{OC} compared to those with the pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film.

The photocurrent hysteresis behaviors of PSCs are further studied. The J – V characteristics of PSCs with either the pristine quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film or the quasi-2D $(\text{PPA})_2(\text{MA})_2\text{Pb}_3\text{I}_{10}$ thin film processed with 3% $\text{Pb}(\text{SCN})_2$ additives under different scan directions with a scan rate of 0.05 V/s are presented in Supporting Information 4. The photocurrent hysteresis behaviors are described by the photocurrent hysteresis index (HI), which is defined as $\text{HI} = \frac{\text{PCE}_{\text{reverse}} - \text{PCE}_{\text{forward}}}{\text{PCE}_{\text{reverse}}}$,⁴¹ where $\text{PCE}_{\text{reverse}}$ and $\text{PCE}_{\text{forward}}$ are

Table 2. Photocurrent Hysteresis Behaviors of PSCs with the Quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ Thin Film

Quasi-2D (PPA) ₂ (MA) ₂ Pb ₃ I ₁₀ thin film	scan ^a direction	<i>J</i> _{sc} (mA/cm ²)	<i>V</i> _{oc} (V)	FF (%)	PCE (%)	HI
processed without Pb(SCN) ₂	forward	13.50	1.12	70	10.58	0.08
	reverse	14.12	1.15	71	11.52	
processed with 3% Pb(SCN) ₂	forward	16.67	1.19	72	14.32	0.04
	reverse	17.25	1.20	72	14.90	

^aThe scan rate is 0.05 V/s.

PCEs observed from the reverse and forward scan directions, respectively. The HI values of PSCs are summarized in Table 2. The PSCs fabricated with the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film possess an HI of 0.08, whereas the PSCs fabricated with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives possess an HI of 0.04. Such suppressed hysteresis is attributed to the reduced grain boundary in the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additive.³

The shelf stabilities of unencapsulated PSCs stored in a glovebox with a nitrogen atmosphere are shown in Figure 7b. PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives retain 60% of their initial PCEs after 600 h, whereas PSCs with the pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film show a degradation after 150 h and degrade more than 50% of their original PCEs after 450 h. Note that PSCs with quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films possess better stability than those with the 3D MAPbI₃ thin film.^{42,43} The enhanced stability of PSCs is attributed to the hydrophobic nature and the pinhole-free quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with 3% Pb(SCN)₂ additives. Unfortunately, both PSCs have a faster degradation at both room temperature and high temperature (Supporting Information 5) compared to those with 2D perovskites with either the Dion–Jacobson phase or alternative cation in the interlayer space phase.^{17,19,20,44,45}

CONCLUSIONS

In conclusion, we have developed novel quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films, where PPA with carbon–carbon triple bond (C≡C) and shorter chain length was employed to form a quasi-2D perovskite structure. PSCs with a pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film exhibited a PCE of 12.16%. To further boost PCEs of PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film, quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films were processed with Pb(SCN)₂ additives. Systematical studies indicated that the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with Pb(SCN)₂ additives possesses larger crystals, superior film morphology, reduced nonradiative recombination, and enhanced and balanced charge-carrier mobilities. As a result, the PSC with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin film processed with Pb(SCN)₂ additives affords a PCE of 15.20% and dramatically suppressed photocurrent hysteresis. Moreover, PSCs with the quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films processed with Pb(SCN)₂ additives exhibited boosted stability compared to those with pristine quasi-2D (PPA)₂(MA)₂Pb₃I₁₀ thin films. All these results demonstrated that we provided an effective approach to realize stable and efficient PSCs with 2D perovskite materials.

ASSOCIATED CONTENT

Supporting Information

The Supporting Information is available free of charge at <https://pubs.acs.org/doi/10.1021/acsami.0c16514>.

TIRFM images of perovskite particles, charge transport properties, PL spectra, photocurrent hysteresis, and thermal stability test (PDF)

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Notes

The authors declare no competing financial interest.

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